

# PRELIMINARY DATA SHEET

# NEC

## NPN SILICON GERMANIUM RF TRANSISTOR

# NESG3031M05

### NPN SiGe RF TRANSISTOR FOR LOW NOISE, HIGH-GAIN AMPLIFICATION FLAT-LEAD 4-PIN THIN-TYPE SUPER MINIMOLD (M05, 2012 PACKAGE)

#### FEATURES

- The device is an ideal choice for low noise, high-gain amplification  
NF = 0.95 dB TYP.,  $G_a = 10.0$  dB TYP. @  $V_{CE} = 2$  V,  $I_c = 6$  mA,  $f = 5.2$  GHz  
NF = 1.1 dB TYP.,  $G_a = 9.5$  dB TYP. @  $V_{CE} = 2$  V,  $I_c = 6$  mA,  $f = 5.8$  GHz
- Maximum stable power gain: MSG = 14.0 dB TYP. @  $V_{CE} = 3$  V,  $I_c = 20$  mA,  $f = 5.8$  GHz
- SiGe HBT technology (UHS3) adopted:  $f_{max} = 110$  GHz
- Flat-lead 4-pin thin-type super minimold (M05, 2012 package)

#### ORDERING INFORMATION

Part Number	Quantity	Supplying Form
NESG3031M05	50 pcs (Non reel)	<ul style="list-style-type: none"> <li>8 mm wide embossed taping</li> <li>Pin 3 (Collector), Pin 4 (Emitter) face the perforation side of the tape</li> </ul>
NESG3031M05-T1	3 kpcs/reel	

**Remark** To order evaluation samples, contact your nearby sales office.  
Unit sample quantity is 50 pcs.

#### ABSOLUTE MAXIMUM RATINGS ( $T_A = +25^{\circ}\text{C}$ )

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	$V_{CBO}$	12.0	V
Collector to Emitter Voltage	$V_{CEO}$	4.3	V
Emitter to Base Voltage	$V_{EBO}$	1.5	V
Collector Current	$I_c$	35	mA
Total Power Dissipation	$P_{tot}^{Note}$	150	mW
Junction Temperature	$T_j$	150	$^{\circ}\text{C}$
Storage Temperature	$T_{stg}$	-65 to +150	$^{\circ}\text{C}$

**Note** Mounted on  $38 \times 38$  mm,  $t = 0.4$  mm polyimide PCB

**Caution** Observe precautions when handling because these devices are sensitive to electrostatic discharge.

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Not all devices/types available in every country. Please check with local NEC Compound Semiconductor Devices representative for availability and additional information.

**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = +25°C)**

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
DC Characteristics						
Collector Cut-off Current	I <sub>CBO</sub>	V <sub>CB</sub> = 5 V, I <sub>E</sub> = 0 mA	–	–	100	nA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> = 1 V, I <sub>C</sub> = 0 mA	–	–	100	nA
DC Current Gain	h <sub>FE</sub> <sup>Note 1</sup>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 6 mA	220	300	380	–
RF Characteristics						
Insertion Power Gain	S <sub>21e</sub>   <sup>2</sup>	V <sub>CE</sub> = 3 V, I <sub>C</sub> = 20 mA, f = 5.8 GHz	6.0	8.5	–	dB
Noise Figure (1)	NF	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 6 mA, f = 5.2 GHz, Z <sub>S</sub> = Z <sub>Sopt</sub> , Z <sub>L</sub> = Z <sub>Lopt</sub>	–	0.95	–	dB
Noise Figure (2)	NF	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 6 mA, f = 5.8 GHz, Z <sub>S</sub> = Z <sub>Sopt</sub> , Z <sub>L</sub> = Z <sub>Lopt</sub>	–	1.1	1.5	dB
Associated Gain (1)	G <sub>a</sub>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 6 mA, f = 5.2 GHz, Z <sub>S</sub> = Z <sub>Sopt</sub> , Z <sub>L</sub> = Z <sub>Lopt</sub>	–	10.0	–	dB
Associated Gain (2)	G <sub>a</sub>	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 6 mA, f = 5.8 GHz, Z <sub>S</sub> = Z <sub>Sopt</sub> , Z <sub>L</sub> = Z <sub>Lopt</sub>	7.5	9.5	–	dB
Reverse Transfer Capacitance	C <sub>re</sub> <sup>Note 2</sup>	V <sub>CB</sub> = 2 V, I <sub>E</sub> = 0 mA, f = 1 MHz	–	0.15	0.25	pF
Maximum Stable Power Gain	MSG <sup>Note 3</sup>	V <sub>CE</sub> = 3 V, I <sub>C</sub> = 20 mA, f = 5.8 GHz	11.0	14.0	–	dB
Gain 1 dB Compression Output Power	P <sub>O</sub> (1 dB)	V <sub>CE</sub> = 3 V, I <sub>C</sub> (set) = 20 mA, f = 5.8 GHz, Z <sub>S</sub> = Z <sub>Sopt</sub> , Z <sub>L</sub> = Z <sub>Lopt</sub>	–	13.0	–	dBm
3rd Order Intermodulation Distortion Output Intercept Point	OIP <sub>3</sub>	V <sub>CE</sub> = 3 V, I <sub>C</sub> (set) = 20 mA, f = 5.8 GHz, Z <sub>S</sub> = Z <sub>Sopt</sub> , Z <sub>L</sub> = Z <sub>Lopt</sub>	–	18.0	–	dBm

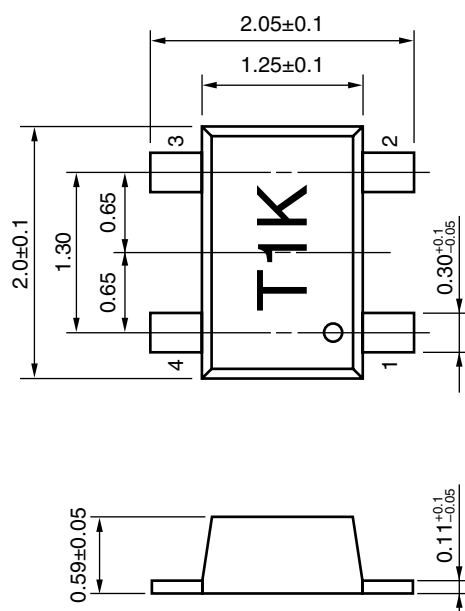
- Notes**
1. Pulse measurement: PW ≤ 350 μs, Duty Cycle ≤ 2%
  2. Collector to base capacitance when the emitter grounded
  3.  $MSG = \left| \frac{S_{21}}{S_{12}} \right|$

**h<sub>FE</sub> CLASSIFICATION**

Rank	FB
Marking	T1K
h <sub>FE</sub> Value	220 to 380

# PACKAGE DIMENSIONS

FLAT-LEAD 4-PIN THIN-TYPE SUPER MINIMOLD (M05, 2012 PACKAGE) (UNIT: mm)



## PIN CONNECTIONS

1. Base
2. Emitter
3. Collector
4. Emitter

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